

# NTK3142P

## Small Signal MOSFET

–20 V, –280 mA, P–Channel with ESD Protection, SOT–723

### Features

- Enables High Density PCB Manufacturing
- 44% Smaller Footprint than SC–89 and 38% Thinner than SC–89
- Low Voltage Drive Makes this Device Ideal for Portable Equipment
- Low Threshold Levels, 1.8 V  $R_{DS(on)}$  Rating
- Low Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics
- Operated at Standard Logic Level Gate Drive, Facilitating Future Migration to Lower Levels Using the Same Basic Topology.
- This is a Pb–Free Device

### Applications

- Interfacing, Switching
- High Speed Switching
- Cellular Phones, PDA's

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain–to–Source Voltage		$V_{DSS}$	–20	V
Gate–to–Source Voltage		$V_{GS}$	$\pm 8.0$	V
Continuous Drain Current (Note 1)	Steady State	$I_D$	$T_A = 25^\circ\text{C}$	–260
			$T_A = 85^\circ\text{C}$	–185
			$T_A = 25^\circ\text{C}$	–280
Power Dissipation (Note 1)	Steady State	$P_D$	$T_A = 25^\circ\text{C}$	400
			$t \leq 5 \text{ s}$	500
Continuous Drain Current (Note 2)	Steady State	$I_D$	$T_A = 25^\circ\text{C}$	–215
			$T_A = 85^\circ\text{C}$	–155
Power Dissipation (Note 2)	Steady State	$P_D$	$T_A = 25^\circ\text{C}$	280
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	$I_{DM}$	–310	mA
Operating Junction and Storage Temperature		$T_J, T_{STG}$	–55 to 150	$^\circ\text{C}$
Source Current (Body Diode) (Note 2)		$I_S$	–240	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface–mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)
2. Surface–mounted on FR4 board using the minimum recommended pad size.

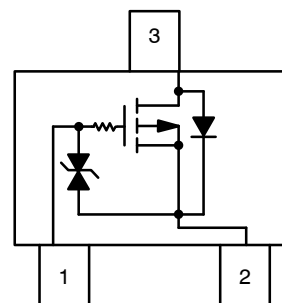


ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	$I_D$ Max
–20 V	2.7 $\Omega$ @ –4.5 V	–280 mA
	4.1 $\Omega$ @ –2.5 V	
	6.1 $\Omega$ @ –1.8 V	

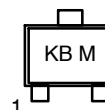
### SOT–723 (3–LEAD)



Top View  
1 – Gate  
2 – Source  
3 – Drain

### MARKING DIAGRAM

  
CASE 631AA  
SOT–723



KB = Specific Device Code  
M = Date Code

### ORDERING INFORMATION

Device	Package	Shipping†
NTK3142PT1G	SOT–723 (Pb–Free)	4000/Tape & Reel 4 mm Pitch
NTK3142PT5G	SOT–723 (Pb–Free)	8000/Tape & Reel 2 mm Pitch

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	315	°C/W
Junction-to-Ambient – $t = 5$ s (Note 3)	$R_{\theta JA}$	250	
Junction-to-Ambient – Steady State Minimum Pad (Note 4)	$R_{\theta JA}$	440	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces)  
4. Surface-mounted on FR4 board using the minimum recommended pad size.

# MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -100\text{ }\mu\text{A}$	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -100\text{ }\mu\text{A}$ , Reference to $25^\circ\text{C}$		14		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = -16\text{ V}$	$T_J = 25^\circ\text{C}$		-1.0	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		-2.0	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			$\pm 1$	$\mu\text{A}$

# ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\text{ }\mu\text{A}$	-0.4		-1.3	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-2.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{ V}, I_D = -260\text{ mA}$		2.9	4.0	$\Omega$
Drain-to-Source On Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{ V}, I_D = -10\text{ mA}$		2.7	3.4	$\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -1\text{ mA}$		4.1	5.3	
		$V_{GS} = -1.8\text{ V}, I_D = -1\text{ mA}$		6.1	10	
Forward Transconductance	$g_{FS}$	$V_{DS} = -5\text{ V}, I_D = -10\text{ mA}$		73		mS

# CAPACITANCES

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = -10\text{ V}$		15.3		pF
Output Capacitance	$C_{OSS}$			4.3		
Reverse Transfer Capacitance	$C_{RSS}$			2.3		

# SWITCHING CHARACTERISTICS, $V_{GS} = 4.5\text{ V}$ (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -5\text{ V}, I_D = -100\text{ mA}, R_G = 6\text{ }\Omega$		8.4	16	ns
Rise Time	$t_r$			15.3	28	
Turn-Off Delay Time	$t_{d(OFF)}$			37.5	80	
Fall Time	$t_f$			22.7	43	

# DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = -10\text{ mA}$	$T_J = 25^\circ\text{C}$	0.69	-1.2	V
			$T_J = 125^\circ\text{C}$	0.56		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, V_{DD} = -20\text{ V}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}, I_S = -1.0\text{ A}$		37	80	ns
Charge Time	$t_a$			15.9	30	
Discharge Time	$t_b$			21.1	50	
Reverse Recovery Charge	$Q_{RR}$			20	70	nC

5. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

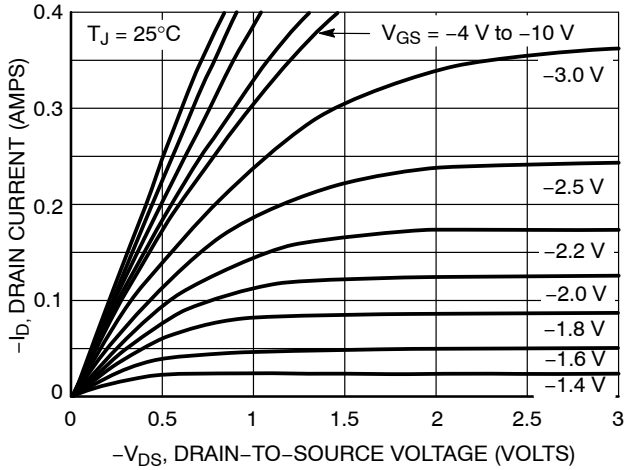


Figure 1. On-Region Characteristics

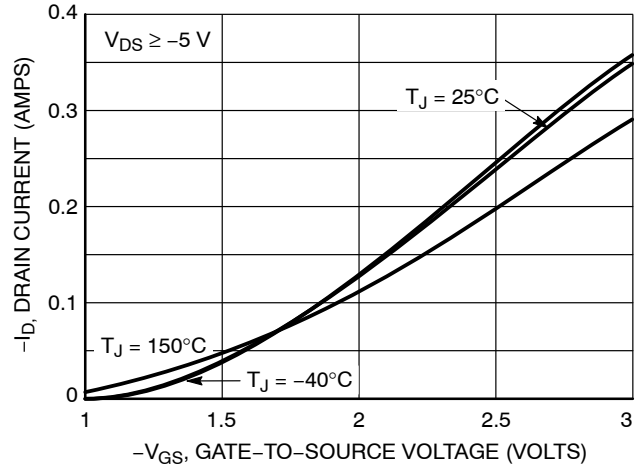


Figure 2. Transfer Characteristics

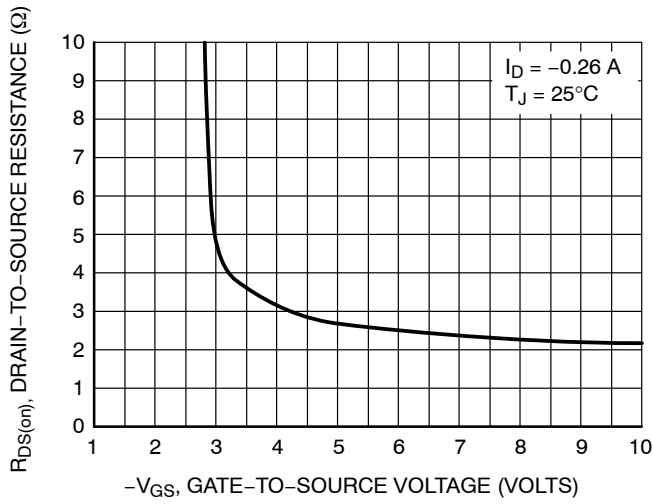


Figure 3. On-Resistance vs. Gate-to-Source Voltage

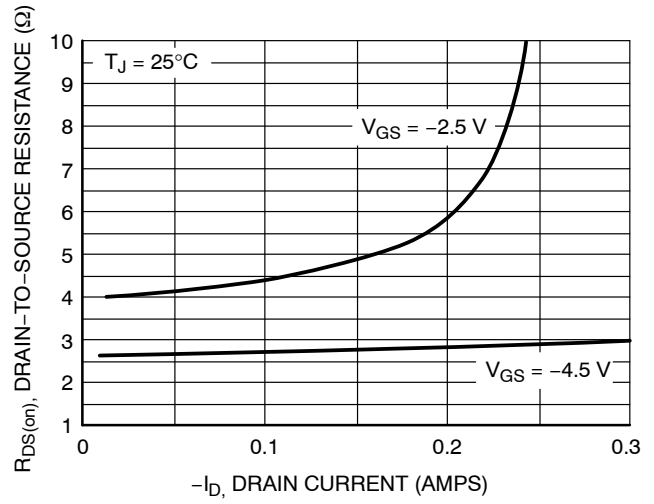


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

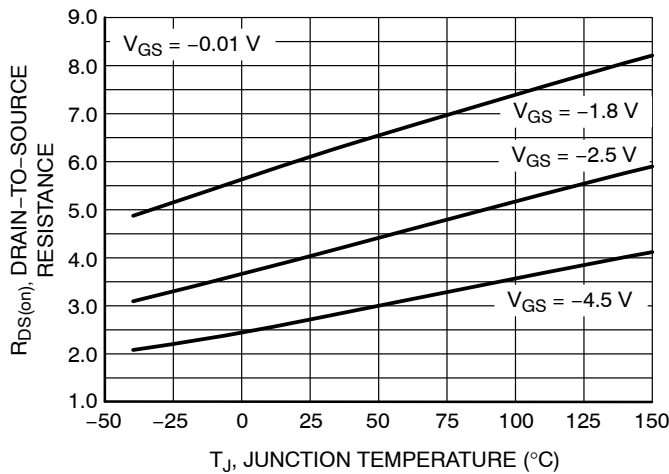


Figure 5. On-Resistance Variation with Temperature

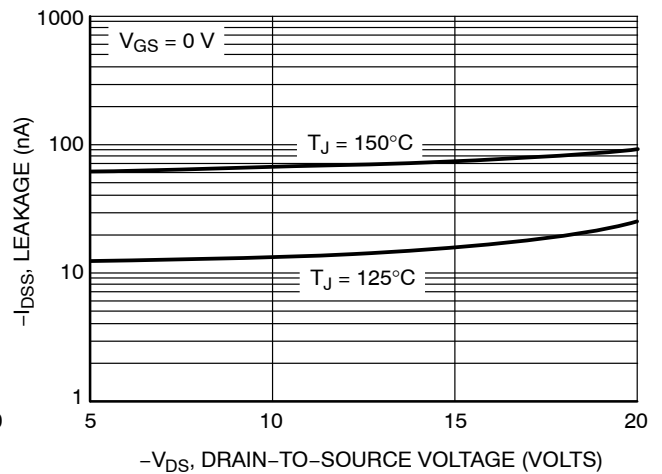


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

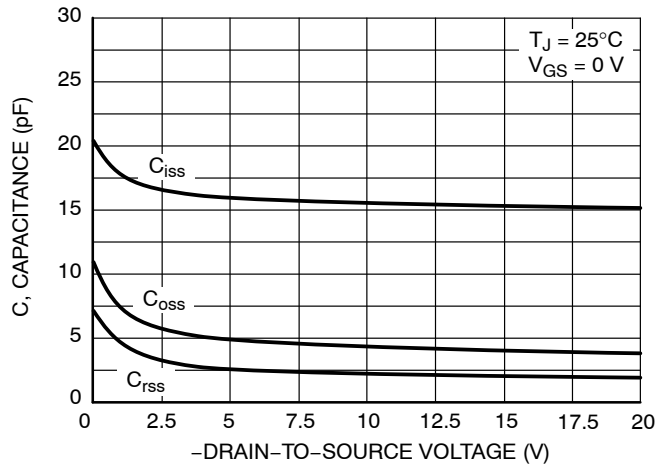


Figure 7. Capacitance Variation

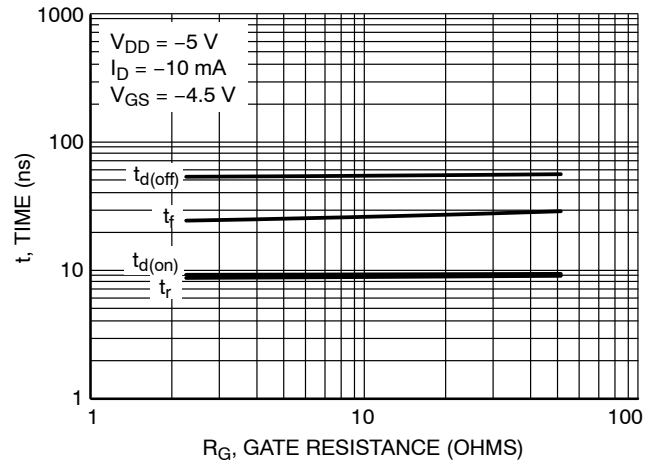


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

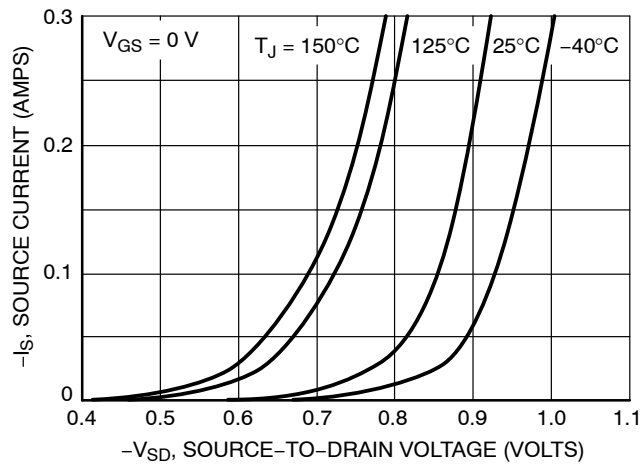
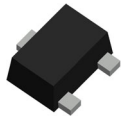


Figure 9. Diode Forward Voltage vs. Current

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

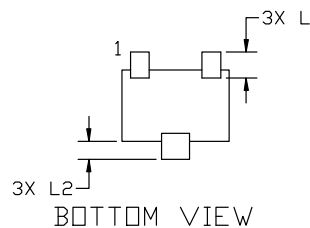
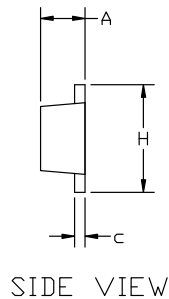
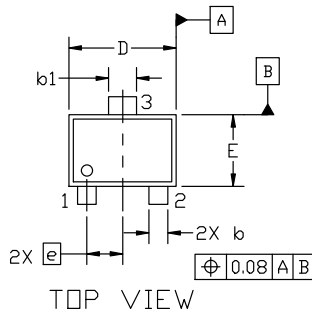


**SOT-723 1.20x0.80x0.50, 0.40P**  
**CASE 631AA**  
**ISSUE E**

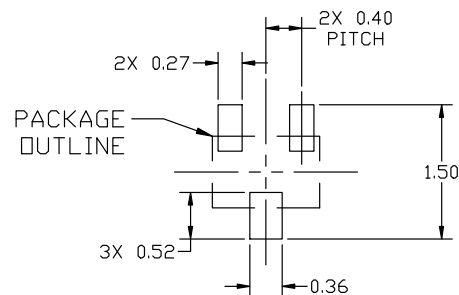
DATE 24 JAN 2024

### NOTES:

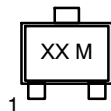
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



### GENERIC MARKING DIAGRAM\*



XX = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN
---	--	--	--	--

<b>DOCUMENT NUMBER:</b>	<b>98AON12989D</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>DESCRIPTION:</b>	<b>SOT-723 1.20x0.80x0.50, 0.40P</b>	<b>PAGE 1 OF 1</b>

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at  
[www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)